Mi-Hee Ji

List of Publications by Year
in descending order

22 papers	454 citations	840776 11 h-index	713466 21 g-index
22 all docs	22 docs citations	22 times ranked	811 citing authors

#	Article	IF	Citations
1	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. Applied Physics Letters, 2012, 101, .	3.3	80
2	Rethinking phonons: The issue of disorder. Npj Computational Materials, 2017, 3, .	8.7	66
3	Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. Journal of Crystal Growth, 2014, 388, 143-149.	1.5	44
4	Al_{<i>x</i>}Ga_{1â^’<i>x</i>}N Ultraviolet Avalanche Photodiodes With Avalanche Gain Greater Than 10^{5}. IEEE Photonics Technology Letters, 2015, 27, 642-645.	2.5	38
5	Demonstration of Large-Size Vertical Ga₂O₃ Schottky Barrier Diodes. IEEE Transactions on Power Electronics, 2021, 36, 41-44.	7.9	38
6	Uniform and Reliable GaN <italic>p-i-n</italic> Ultraviolet Avalanche Photodiode Arrays. IEEE Photonics Technology Letters, 2016, 28, 2015-2018.	2.5	26
7	Comparison of AlGaN pâ€“iâ€“n ultraviolet avalanche photodiodes grown on free-standing GaN and sapphire substrates. Applied Physics Express, 2015, 8, 122202.	2.4	23
8	p-i-p-i-n Separate Absorption and Multiplication Ultraviolet Avalanche Photodiodes. IEEE Photonics Technology Letters, 2018, 30, 181-184.	2.5	23
9	GaN/InGaN avalanche phototransistors. Applied Physics Express, 2015, 8, 032101.	2.4	20
10	Temperature-Dependent Characteristics of GaN Homojunction Rectifiers. IEEE Transactions on Electron Devices, 2015, 62, 2679-2683.	3.0	19
11	Temperature-Dependent Leakage Current Characteristics of Homojunction GaN p-i-n Rectifiers Using Ion-Implantation Isolation. IEEE Transactions on Electron Devices, 2019, 66, 4273-4278.	3.0	15
12	Structural and Electrical Characterization of 2â€•Ammonothermal Free-Standing GaN Wafers. Progress toward Pilot Production. Materials, 2019, 12, 1925.	2.9	10
13	Direct periodic patterning of GaN-based light-emitting diodes by three-beam interference laser ablation. Applied Physics Letters, 2014, 104, 141105.	3.3	9
14	Thermal and radiation response of 4Hâ€“SiC Schottky diodes with direct-write electrical contacts. Applied Physics Letters, 2020, 116, .	3.3	9
15	Raman Scattering Study of Lattice Vibrations in the Type-II Superlattice <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:mi>InAs</mml:mi><mml:mo>/</mml:mo><mml:msub><mml:mrow><mml:mi>InAs</mml:mi></m Physical Review Applied, 2017, 8, .	3.8	7
16	Flexible single-crystalline GaN substrate by direct deposition of III-N thin films on polycrystalline metal tape. Journal of Materials Chemistry C, 2021, 9, 2243-2251.	5.5	6
17	Effect of Group-III precursors on unintentional gallium incorporation during epitaxial growth of InAlN layers by metalorganic chemical vapor deposition. Journal of Applied Physics, 2015, 118, .	2.5	5
18	Direct metal contacts printing on 4H-SiC for alpha detectors and inhomogeneous Schottky barriers. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 989, 164961.	1.6	4

#	Article	IF	Citations
19	Large area vertical Ga2O3 Schottky diodes for X-ray detection. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2021, 1013, 165664.	1.6	4
20	Effect of latticeâ€matched InAlGaN electronâ€blocking layer on hole transport and distribution in InGaN/GaN multiple quantum wells of visible lightâ€emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1296-1301.	1.8	3
21	Demonstration of uniform and reliable GaN p-i-p-i-n separate-absorption and multiplication ultraviolet avalanche photodiode arrays with large detection area. , 2019, , .		3
22	Improved Hole Transport by ${m p}hbox{-}{m In}_{x}{m Ga}_{1-x}{m N}$ Layer in Multiple Quantum Wells of Visible LEDs. IEEE Photonics Technology Letters, 2013, 25, 1789-1792.	2.5	2